

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









# **BF1107**

# N-channel single gate MOSFET Rev. 04 — 9 January 2007

**Product data sheet** 

## **Product profile**

#### 1.1 General description

The BF1107 is a depletion type field-effect transistor in a SOT23 package. The low loss and high isolation capabilities of this MOSFET provide excellent RF switching functions. Integrated diodes between gate and source and between gate and drain protect against excessive input voltage surges. Drain and source are interchangeable.

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

#### 1.2 Features

Currentless RF switch

#### 1.3 Applications

- Various RF switching applications such as:
  - Passive loop through for VCR tuner
  - Transceiver switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$L_{ins(on)}$ on-state insertion loss		$V_{SG} = V_{DG} = 0 \text{ V};$ f = 50 MHz to 860 MHz				
	$R_S = R_L = 50 \Omega$	-	-	2.5	dB	
		$R_S = R_L = 75 \Omega$	-	-	3.5	dB
ISL <sub>off</sub> off-state isolation		$V_{SG} = V_{DG} = 5 \text{ V};$ f = 50 MHz to 860 MHz				
	$R_S = R_L = 50 \Omega$	30	-	-	dB	
		$R_S = R_L = 75 \Omega$	30	-	-	dB
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 0 \text{ V}; I_D = 1 \text{ mA}$	-	12	20	Ω
$V_{GS(p)}$	gate-source pinch-off voltage	$V_{DS} = 1 \text{ V}; I_D = 20 \mu\text{A}$	-	-3	-4.5	V



#### N-channel single gate MOSFET

# 2. Pinning information

Table 2. Discrete pinning

Pin	Description		Simplified outline	Symbol
1	drain	[1]		
2	source	[1]	3	ل_
3	gate		1 2	3 — 2 sym120

<sup>[1]</sup> Drain and source are interchangeable

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BF1107	-	plastic surface-mounted package; 3 leads	SOT23

## 4. Marking

Table 4. Marking

Type number	Marking code
BF1107	S3p

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	3	V
$V_{SD}$	source-drain voltage		-	3	V
$V_{DG}$	drain-gate voltage		-	7	V
$V_{SG}$	source-gate voltage		-	7	V
$I_D$	drain current		-	10	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

#### N-channel single gate MOSFET

## 6. Thermal characteristics

		_	
Table 6	Thermal	charact	eristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[1] 260	K/W

<sup>[1]</sup> Soldering point of the gate lead.

## 7. Static characteristics

Table 7. Static characteristics

 $T_i = 25 \,^{\circ}C$ .

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)GSS}$	gate-source breakdown voltage	$V_{DS} = 0 \text{ V}; I_{GS} = 0.1 \text{ mA}$	7	-	-	V
V <sub>GS(p)</sub>	gate-source pinch-off voltage	$V_{DS} = 1 \text{ V}; I_D = 20 \mu\text{A}$	-	-3	-4.5	V
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = -5 \text{ V}; V_{DS} = 2 \text{ V}$	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -5 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nA

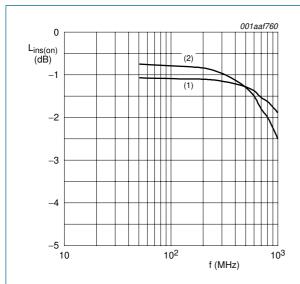
# 8. Dynamic characteristics

Table 8. Dynamic characteristics

Common gate;  $T_{amb} = 25 \,^{\circ}$ C.

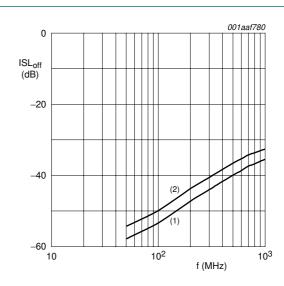
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L <sub>ins(on)</sub>	on-state insertion loss	$V_{SG} = V_{DG} = 0 \text{ V}$ ; f = 50 MHz to 860 MHz				
		$R_S = R_L = 50 \Omega$	-	-	2.5	dB
	$R_S = R_L = 75 \Omega$	-	-	3.5	dB	
ISL <sub>off</sub> off-state isolation		$V_{SG} = V_{DG} = 5 \text{ V}; f = 50 \text{ MHz to } 860 \text{ MHz}$				
		$R_S = R_L = 50 \Omega$	30	-	-	dB
	$R_S = R_L = 75 \Omega$	30	-	-	dB	
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 0 \text{ V}; I_D = 1 \text{ mA}$	-	12	20	Ω
C <sub>ig</sub>	input capacitance at gate	f = 1 MHz				
		$V_{SG} = V_{DG} = 5 V$	-	0.9	-	рF
	$V_{SG} = V_{DG} = 0 V$	-	1.5	2	pF	
C <sub>og</sub>	output capacitance at gate	f = 1 MHz				
		$V_{SG} = V_{DG} = 5 V$	-	0.9	-	рF
		$V_{SG} = V_{DG} = 0 V$	-	1.5	2	pF

#### N-channel single gate MOSFET



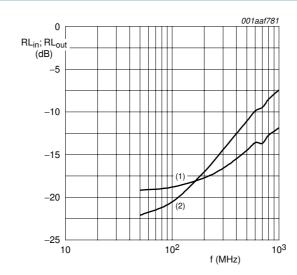
- (1)  $R_S = R_L = 50 \Omega$
- (2)  $R_S = R_L = 75 \Omega$  $V_{SG} = V_{DG} = 0 V$

Fig 1. On-state insertion loss as a function of frequency; typical values



- (1)  $R_S = R_L = 50 \Omega$
- (2)  $R_S = R_L = 75 \Omega$  $V_{SG} = V_{DG} = 5 V$

Fig 2. Off-state isolation as a function of frequency; typical values



- (1)  $R_S = R_L = 50 \Omega$
- (2)  $R_S = R_L = 75 \Omega$  $V_{SG} = V_{DG} = 0 V$

Fig 3. Input and output return loss (on-state) as a function of frequency; typical values

#### **N-channel single gate MOSFET**

# 9. Package outline

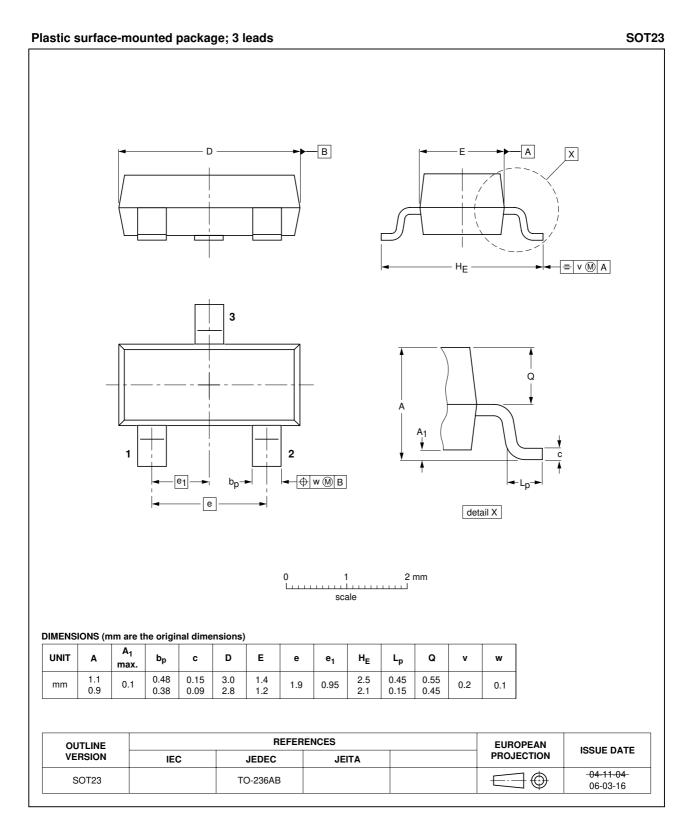


Fig 4. Package outline SOT23

## N-channel single gate MOSFET

## 10. Abbreviations

#### Table 9. Abbreviations

Acronym	Description
MOSFET	Metal-Oxide Semiconductor Field-Effect Transistor
RF	Radio Frequency
VCR	Videocassette Recorder

# 11. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF1107_4	20070109	Product data sheet	-	BF1107_1107W_3
Modifications:		of this data sheet has been roof NXP Semiconductors.	edesigned to comply v	vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the ne	w company name whe	ere appropriate.
	<ul> <li>Symbol not Semicondu</li> </ul>	ation has been adapted to co ctors.	mply with the current	guidelines of NXP
	<ul> <li>Product typ</li> </ul>	e BF1107W has been remove	ed from this data shee	t.
BF1107_1107W_3 (9397 750 05776)	19990514	Product data sheet	-	BF1107_2
BF1107_2 (9397 750 03969)	19980622	Product data sheet	-	BF1107_N_1
BF1107_N_1 (9397 750 03695)	19980407	Preliminary data sheet	-	-

#### N-channel single gate MOSFET

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

#### 12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

#### 12.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

#### 12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 13. Contact information

For additional information, please visit: http://www.nxp.com

For sales office addresses, send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

#### **N-channel single gate MOSFET**

## 14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information 2
4	Marking
5	Limiting values
6	Thermal characteristics 3
7	Static characteristics 3
8	Dynamic characteristics 3
9	Package outline 5
10	Abbreviations 6
11	Revision history 6
12	Legal information 7
12.1	Data sheet status
12.2	Definitions 7
12.3	Disclaimers
12.4	Trademarks 7
13	Contact information 7
14	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2007.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 9 January 2007 Document identifier: BF1107\_4